L Number	Hits	Search Text	DB	Time stamp
11	10	(("5397905") or ("5313082") or ("6638827") or ("6531355") or	USPAT	2004/10/28 22:39
		("6306711") or ("5521105") or ("5485027") or ("5482888") or		
		("5070377") or ("6489653")).PN.		
12	3	(("5397905") or ("6638827") or ("6489653")).PN.	USPAT	2004/10/28 22:39
-	1632	438/197.ccls. or 438/299.ccls. or 438/301.ccls.	USPAT	2004/10/28 22:35
-	146	semiconductor and drain and source and (gate adj electrode)	USPAT	2004/10/25 18:30
		and (gate adj insulation) and buried and (PN adj junction)		
-	2	(high adj impurity) and (low adj impurity) and gate and ((buried	USPAT	2004/10/25 18:32
		adj layer) with (PN adj junction))		
-	162	((buried adj layer) with (PN adj junction))	USPAT	2004/10/25 18:32
-	862	438/286.ccls. or 257/409.ccls.	USPAT	2004/10/26 18:19
-	437	(438/286.ccls. or 257/409.ccls.) and (breakdown or (break adj	USPAT	2004/10/26 18:19
		down))		
-	145	(438/286.ccls. or 257/409.ccls.) and (PN adj junction)	USPAT	2004/10/26 18:19
-	7606	((break adj down) or breakdown) and (MOS with transistor)	USPAT	2004/10/26 18:20
-	1442	(((break adj down) or breakdown) and (MOS with transistor))	USPAT	2004/10/26 18:20
į	4740	and (PN adj junction)		000440/004004
-	4713	(((break adj down) or breakdown) and (MOS with transistor))	USPAT	2004/10/26 18:21
	4550	and ((p adj type) or (p-type))	LICDAT	0004/40/00 40:04
-	4553	((((break adj down) or breakdown) and (MOS with transistor))	USPAT	2004/10/26 18:21
	4004	and ((p adj type) or (p-type))) and gate	USPAT	2004/10/28 21:07
-	4204	(((((break adj down) or breakdown) and (MOS with transistor))	USPAT	2004/10/20 21.07
	2481	and ((p adj type) or (p-type))) and gate) and (source and drain) ((((((break adj down) or breakdown) and (MOS with transistor))	USPAT	2004/10/26 18:22
-	2401	and ((p adj type) or (p-type))) and gate) and (source and	USFAI	2004/10/20 10.22
		drain)) and (impurity)		
L _	12	((((((((break adj down) or breakdown) and (MOS with	USPAT	2004/10/26 18:23
	12	transistor)) and ((p adj type) or (p-type))) and gate) and	00.70	2004/10/20 10:20
		(source and drain)) and (impurity)) and ((source or drain) with		
		engineering)		
_	1809	(((((((break adj down) or breakdown) and (MOS with	USPAT	2004/10/28 21:01
	.550	transistor)) and ((p adj type) or (p-type))) and gate) and		
		(source and drain)) and (impurity)) and ((breakdown or (break		
		adj down)) adj voltage)		